PCN Number:		201	50316	5002					PCN D	ate:	03/20/2015	
Titl	Title: Add Cu as Alternative Wire Base Metal for Selected Device(s)											
Cus	tom	er Conta	act:	PCN A	Manager		Dept:	Quality Services				
Proposed 1 st Ship Date: 06/20				/20	016	Estimated Sample Date provided a Availability: sample request			•			
Cha	Change Type:											
	Asse	embly Sit	:e				Design			Wafer Bump Site		
\boxtimes	Asse	embly Pro	ocess				Data Sheet			Wafe	r Bum	p Material
\boxtimes	Asse	embly Ma	iteria	ls			Part number change			Wafe	r Bum	p Process
Mechanical Specification					Test Si	te		Wafer Fab Site				
Packing/Shipping/Labeling					Test Process			Wafe	r Fab	Materials		
								Wafe	r Fab	Process		
	PCN Details											

Description of Change:

Texas Instruments is pleased to announce the qualification of Cu as an additional bond wire option for devices listed in "Product affected" section below. Devices will remain in current assembly facilities and there will be no other piece part changes:

Pkg Family	Wire From	Wire To
JRBGA	Au, 0.96 mil	Cu, 0.8 mil
QFN	Au, 0.96 mil, 1.3 mil, 1.97mil	Cu, 0.8 mil, 0.96 mil, 1.98 mil
SOIC	Au, 0.9 mil, 1.15 mil, 1.31 mil	Cu, 0.96 mil
SOP	Au, 1.15 mil	Cu, 0.96 mil
SSOP	Au, 0.96 mil	Cu, 0.96 mil
TQFP	Au, 0.8 mil, 0.96 mils	Cu, 0.8 mil, 0.96 mil
TSSOP	Au, 0.96 mil	Cu, 0.96 mil
TVSOP	Au, 0.8 mil	Cu, 0.96 mil
UBGA	Au, 0.96 mil	Cu, 0.8 mil

Reason for Change:

Continuity of supply.

- 1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
- 2) Maximize flexibility within our Assembly/Test production sites.
- 3) Cu is easier to obtain and stock

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

None

Product Affected:

DEVICE	PKG FAMILY	DEVICE	PKG FAMILY
CDCUN1208LPRHBR	QFN	SN74LVC00ADT	SOIC
CDCUN1208LPRHBT	QFN	SN75LVDS83CZQLR	JRBGA
HPABUS13RPFCR	TQFP	TCA9554PWR	TSSOP
OPA2335AID	SOIC	TMDS442PNP	TQFP
OPA2335AIDG4	SOIC	TMDS442PNPG4	TQFP

OPA2335AIDR	SOIC	TPA6120A2RGYR	QFN
OPA2335AIDRG4	SOIC	TPA6120A2RGYT	QFN
PCI2050BZHK	UBGA	TPS544C20RVFR	QFN
PCM1803DBR	SSOP	TPS544C20RVFT	QFN
SN65HVD72D	SOIC	TPS544C24RVFR	QFN
SN65HVD72DR	SOIC	TPS544C24RVFT	QFN
SN65HVD75D	SOIC	TPS74301RGWR	QFN
SN65HVD75DR	SOIC	TPS74301RGWRG4	QFN
SN74AVC8T245DGVR-P	TVSOP	TPS74301RGWT	QFN
SN74LVC00AD	SOIC	TPS74301RGWTG4	QFN
SN74LVC00ADE4	SOIC	TUSB8040PFP	TQFP
SN74LVC00ADG4	SOIC	TUSB9261PVP	TQFP
SN74LVC00ADR	SOIC	TUSB9261PVPT	TQFP
SN74LVC00ADRE4	SOIC	ULN2003AINSR	SOP
SN74LVC00ADRG4	SOIC		



TI Information Selective Disclosure

Qualification Report

Copper wire bonding Qualification on Aluminum Bond Pads Approved 07/07/2011

Product Attributes

Attribute s	Qual Device: ADS1230I PW	Qual Device: DRV590G QC	Qual Device: F741900A PFB	Qual Device: SN75DP139 RGZ	Qual Device: THS7303 PW	Qual Device: TPA5050 RSA	Qual Device: TSB12LV21B PGF	Qual Device: TSB81BA3E PFP	Qual Device: TVAIC3106IZ QER
Assembly Site	TAI	TAI	TAI	MLA	TAI	MLA	PHI	TAI	PHI
Package Family	TSSOP	JRBGA	TQFP	VQFN	TSSOP	VQFN	LQFP	TQFP	JRBGA
Flammabi lity Rating	1 III Q/I (/_/) 1	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Site	DMOS5	DFAB	DMOS5	FFAB	FFAB	DMOS5	DMOS5	DMOS5	DMOS5
Wafer Fab Process	50HPA07X3	LBC3S	1833C05X4	BICOM3XL	ВІСОМ3	1833C05X4	33C12X3	1833C05X4	1833C05.24LR D

- QBS: Qual By Similarity
- Qual Devices qualified at LEVEL2-260C: ADS1230IPW, SN75LVDS84ADGG, THS7303PW, TPA5050RSA
- Qual Device DRV590GQC is qualified at LEVEL2A-235C
- Qual Devices qualified at LEVEL3-250C: F741900APFB, SN75DP139RGZ, TSB81BA3EPFP, TVAIC3106IZQER



Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Ty pe	Test Name / Conditi on	Durat ion	Qual Device: ADS123 0IPW	Qual Device: DRV590 GQC	Qual Device: F741900 APFB	Qual Device: SN75DP13 9RGZ	Qual Device: THS730 3PW	Qual Device: TPA5050 RSA	Qual Device: TSB12LV21 BPGF	Qual Device: TSB81BA3 EPFP	Qual Device: TVAIC3106I ZQER
AC	Autoclav e 121C	96 Hours	3/231/0	-	-	1/77/0	-	3/230/0	-	3/231/0	-
UHA ST	Unbiased HAST 110C/85 %RH	264 Hours	-	-	-	-	-	-	-	-	3/231/0
UHA ST	Unbiased HAST 130C/85 %RH	96 Hours	-	-	-	-	-	-	-	-	-
тс	Temperat ure Cycle, - 55/125C	700 Cycles	-	1/77/0	-	-	-	-	3/231/0	-	3/231/0
тс	Temperat ure Cycle, - 65/150C	500 Cycles	3/231/0	-	3/231/0	1/77/0	3/231/0	3/231/0	3/231/0	3/231/0	-
HTS L	High Temp. Storage Bake, 150C	1000 Hours	-	-	-	-	-	-	-	-	3/231/0
HTS L	High Temp. Storage Bake, 170C	420 Hours	3/231/0	-	3/231/0	1/77/0	3/231/0	3/231/0	3/270/0	3/231/0	-

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Green/Pb-free Status:

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

⁻ The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

⁻ The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

Qualification Report

Copper wire bonding on Aluminum Bond Pads - (VQFN, VSON & WSON Packages) Approved 07/01/2011

Product Attributes

Attributes	Qual Device: DRV401AIRG W	Qual Device: SN75DP122ART Q	Qual Device: TLVDAC32IRHB R	Qual Device: TPA2005D1DR B	Qual Device: TPS51217DSC R	Qual Device: TPS51621RH A
Assembly Site	CLARK-AT	CLARK-AT	CLARK-AT	CLARK-AT	CLARK-AT	CLARK-AT
Package Family	VQFN	VQFN	VQFN	VSON	WSON	VQFN
Flammabilit y Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	Class UL94-V0	UL 94 V-0	UL 94 V-0
Wafer Fab Site	DMOS5	FFAB	DMOS5	FR-BIP-1	RFAB	DFAB
Wafer Fab Process	50HPA07	50BICOM3XL	1833C05X4	3370A12X3	LBC7	LBC4

⁻ QBS: Qual By Similarity

⁻ Qual Devices qualified at LEVEL2-260C: DRV401AIRGW, TLVDAC32IRHBR, TPA2005D1DRB, TPS51217DSCR, TPS51217DSC

⁻ Qual Devices qualified at LEVEL3-260C: SN75DP122ARTQ, TPS51621RHA

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condi tion	Durati on	Qual Device: DRV401AI RGW	Qual Device: SN75DP122 ARTQ	Qual Device: TLVDAC32I RHBR	Qual Device: TPA2005D 1DRB	Qual Device: TPS51217 DSCR	Qual Device: TPS5162 1RHA
AC	Autocla ve 121C	96 Hours	3/229/0	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0
TC	Temper ature Cycle - 65/150 C	500 Cycles	3/230/0	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0	3/231/0
BHAST	Bias HAST 130C 85%RH	96 Hours	-	-	-	-	3/231/0	-
MQ	Manufa cturabili ty (Assem bly)		Pass	Pass	Pass	Pass	Pass	Pass

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:



Qualification Report

Qualification 0.95 mils Wire Diameter- Cu Approved 09/19/2012

Product Attributes

Attributes	Qual Device: MAX232DR	Qual Device: RC4558DR	Qual Device: SN74LV14ADR	Qual Device: ULN2003ADR
Assembly Site	MLA (TIM)	MLA (TIM)	MLA (TIM)	MLA (TIM)
Package Family	SOIC	SOIC	SOIC	SOIC
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Site	SFAB	SFAB	SFAB	SFAB
Wafer Fab Process	LBC3S	JI1-Lin	EPIC1-S_SLM	JI-SLM

⁻ QBS: Qual By Similarity

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: MAX232DR	Qual Device: RC4558DR	Qual Device: SN74LV14ADR	Qual Device: ULN2003ADR
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0	1/77/0	1/77/0	1/77/0
AC	Autoclave 121C	96 Hours	3/231/0	1/77/0	1/77/0	1/77/0
TC	Temperature Cycle, - 65/150C	500 Cycles	3/231/0	3/231/0	3/231/0	3/231/0
HTSL	High Temp Storage Bake 150C	1000 Hours	-	3/231/0	3/231/0	-
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	-	-	3/231/0
HTOL	Life Test, 150C	300 Hours	3/231/0	1/77/0	1/77/0	1/77/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	Pass	Pass
	Bond Strength	Wires	3/228/0	1/76/0	1/76/0	1/76/0
DPA	Lead Pull to Destruction	Leads	3/66/0	1/22/0	1/22/0	1/22/0
FLAM	Flammability (IEC 695-2-2)		3/15/0	1/5/0	1/5/0	-
FLAM	Flammability (UL 94V-0)		3/15/0	1/5/0	1/5/0	-
FLAM	Flammability (UL- 1694)		3/15/0	1/5/0	1/5/0	-
MQ	Manufacturability	(per mfg. Site specification)	Pass	Pass	Pass	Pass
MSL	Moisture Sensitivity, JEDEC	Level 1-260C	3/36/0	3/36/0	3/36/0	3/36/0
XRAY	X-ray	(top side only)	3/15/0	1/5/0	1/5/0	1/5/0

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Green/Pb-free Status:

⁻ Qual Devices qualified at LEVEL1-260C: MAX232DR, RC4558DR, SN74LV14ADR, ULN2003ADR

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

⁻ The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

⁻ The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/



Qualification Report

Analog Cu wire enterprise qualification

Approved 09/11/2014

Product Attributes

Attributes	Qual Device: UCD9246FRGCR
Assembly Site	CLARK-AT
Package Family	VQFN
Flammability Rating	UL 94 V-0
Wafer Fab Supplier	TSMC 11
Wafer Fab Process	0.18UM-TSMC

⁻ QBS: Qual By Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: UCD9246FRGCR
AC	Autoclave 121C	96 Hours	3/231/0
UHAST	Unbiased HAST 110C/85%RH	96 Hours	3/231/0
TC	Temperature Cycle, - 65/+150C	500 Cycles	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0
MQ	Manufacturability	(per mfg Site specification)	Pass

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Green/Pb-free Status:

⁻ Qual Device UCD9246FRGCR is qualified at LEVEL3-260C

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

⁻ The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

⁻ The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

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